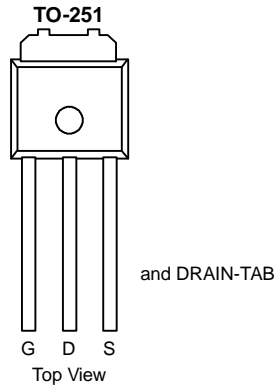




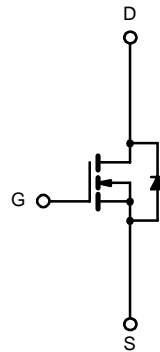
N-Channel 30-V (D-S), 175°C, MOSFET PWM Optimized

175°C Rated
Maximum Junction Temperature
TrenchFET®
Power MOSFETS

PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^a
30	0.010 @ $V_{GS} = 10$ V	20
	0.014 @ $V_{GS} = 4.5$ V	18



Order Number:
SUU50N03-10P



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	A
		$T_A = 100^\circ\text{C}$	
Pulsed Drain Current	I_{DM}	100	A
Continuous Source Current (Diode Conduction) ^a	I_S	20	
Maximum Power Dissipation	P_D	$T_C = 25^\circ\text{C}$	W
		$T_A = 25^\circ\text{C}$	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	15	$^\circ\text{C/W}$
		Steady State	40	
Maximum Junction-to-Case	R_{thJC}	1.75	2.1	

Notes:

- a. Surface mounted on 1" x 1" FR4 Board, $t \leq 10$ sec.
- b. See SOA curve for voltage derating.



MOSFET SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _{DS} = 250 μA	1	2		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 175 °C			150	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 15 A		0.0075	0.010	Ω
		V _{GS} = 10 V, I _D = 15 A, T _J = 125 °C			0.016	
		V _{GS} = 10 V, I _D = 15 A, T _J = 175 °C			0.019	
		V _{GS} = 4.5 V, I _D = 15 A		0.011	0.014	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 15 A	20			S
Dynamic^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		2710	6000	pF
Output Capacitance	C _{oss}			500		
Reverse Transfer Capacitance	C _{rss}			250		
Total Gate Charge ^c	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 20 A		55	100	nC
Gate-Source Charge ^c	Q _{gs}			10		
Gate-Drain Charge ^c	Q _{gd}			9		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 15 V, R _L = 0.3 Ω I _D = 20 A, V _{GEN} = 10 V, R _g = 2.5 Ω		16	30	ns
Rise Time ^c	t _r			90	135	
Turn-Off Delay Time ^c	t _{d(off)}			33	60	
Fall Time ^c	t _f			20	40	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)^b						
Continuous Current	I _S				20	A
Pulsed Current	I _{SM}				100	
Forward Voltage ^a	V _{SD}	I _F = 100 A, V _{GS} = 0 V		1.2	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		55	100	ns

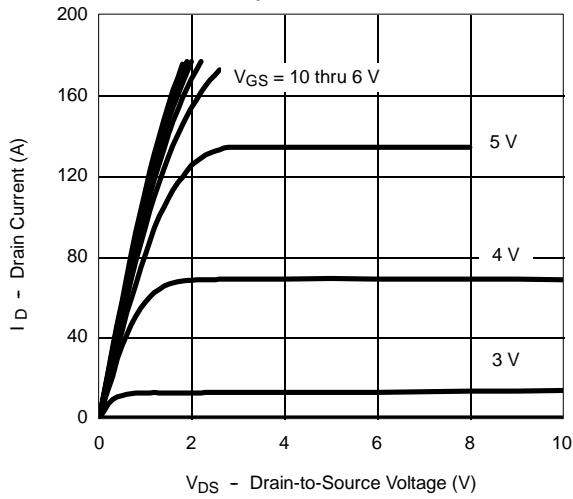
Notes:

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

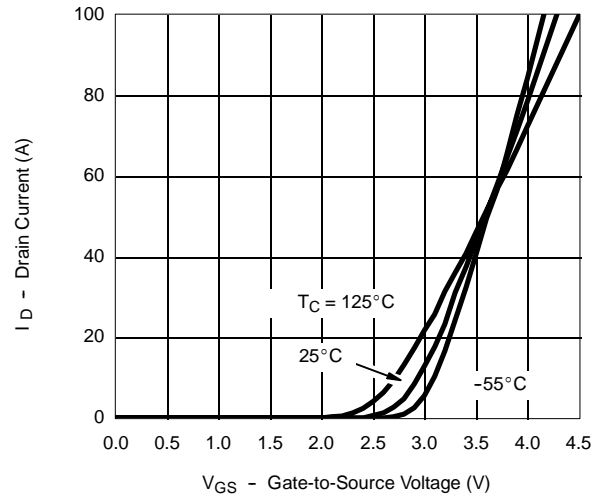


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

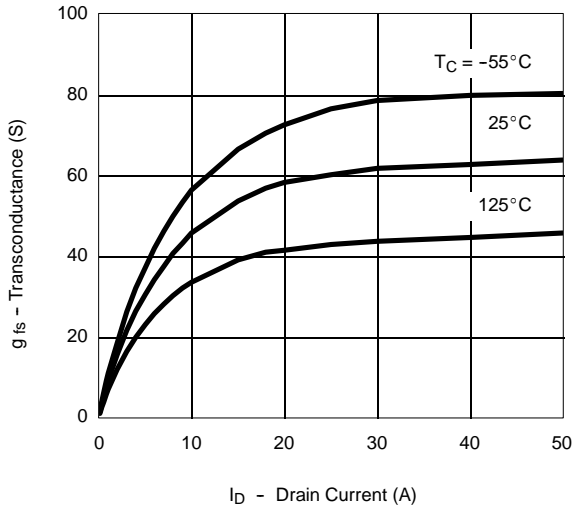
Output Characteristics



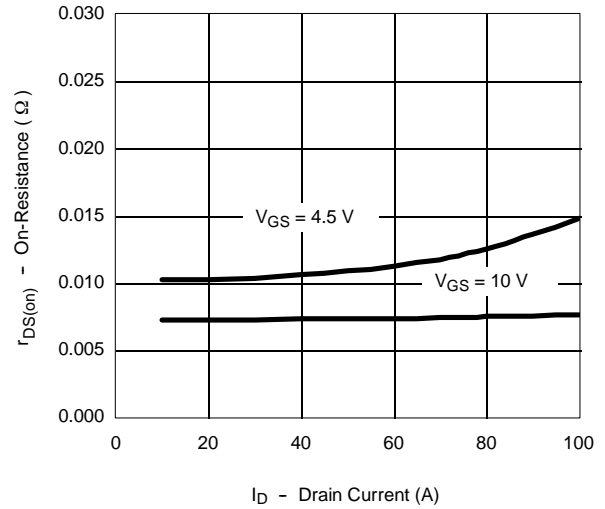
Transfer Characteristics



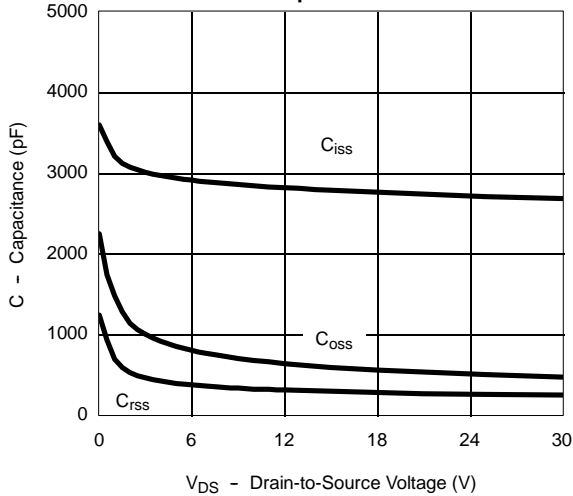
Transconductance



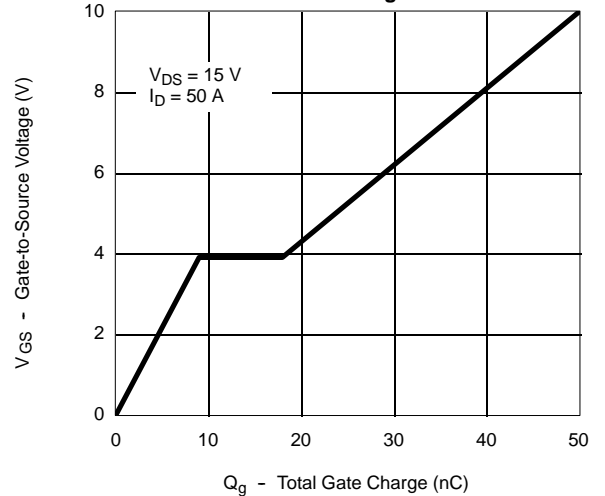
On-Resistance vs. Drain Current



Capacitance

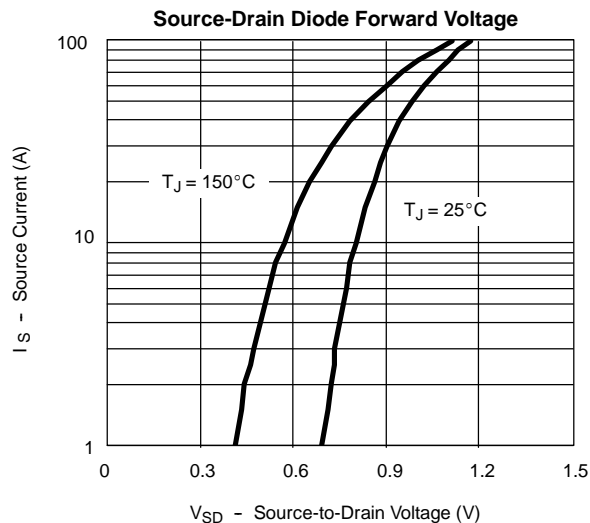
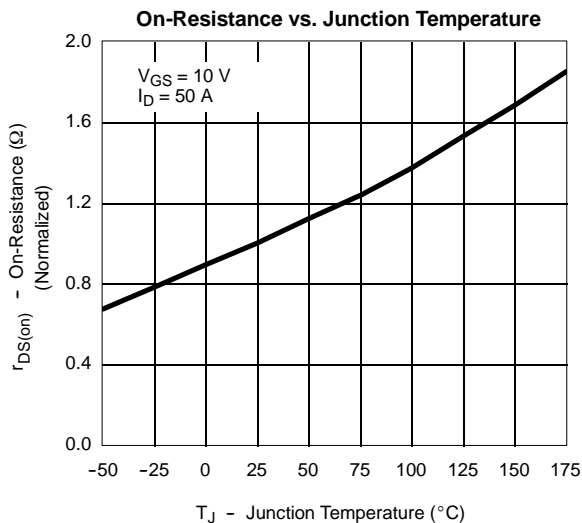


Gate Charge





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



THERMAL RATINGS

